

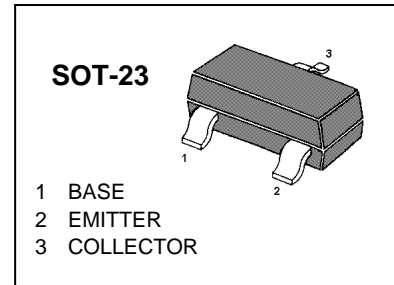
# S8550

## TRANSISTOR(PNP)

### FEATURES

Complimentary to S8050

Collector current:  $I_C=0.5A$



**MARKING : 2TY**

### MAXIMUM RATINGS ( $T_A=25^\circ C$ unless otherwise noted)

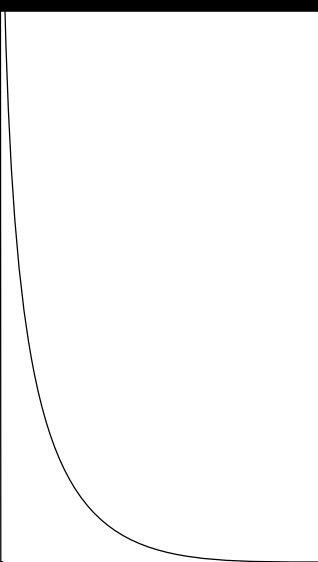
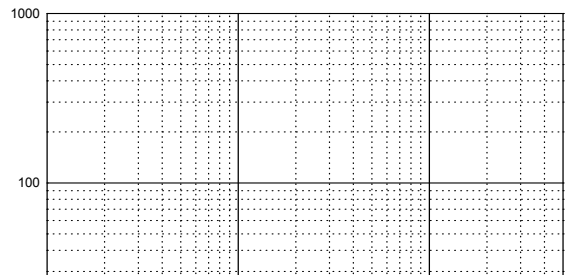
Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-25	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-0.5	A
$P_C$	Collector Power Dissipation	0.3	W
$T_j$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-55-150	$^\circ C$

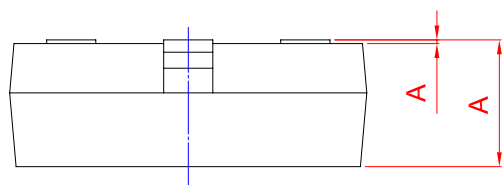
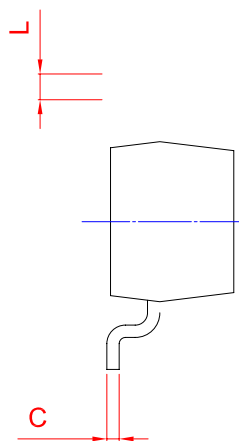
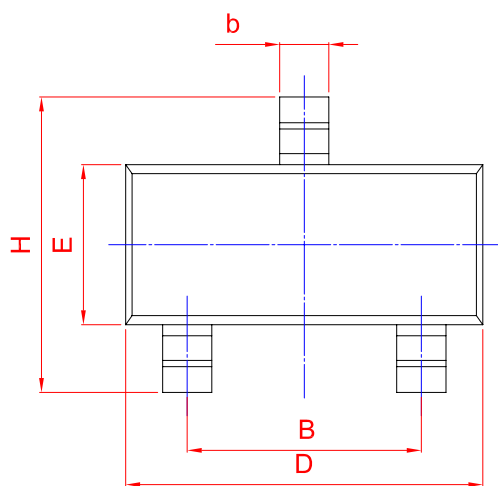
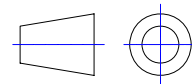
### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
<b>Collector-base breakdown voltage</b>	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E=0$	-40		V
<b>Collector-emitter breakdown voltage</b>	$V_{(BR)CEO}$	$I_C = -1mA, I_B=0$	-25		V
<b>Emitter-base breakdown voltage</b>	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C=0$	-5		V
<b>Collector cut-off current</b>	$I_{CBO}$	$V_{CB} = -40V, I_E=0$		-0.1	$\mu A$
<b>Collector cut-off current</b>	$I_{CEO}$	$V_{CE} = -20V, I_B=0$		-0.1	$\mu A$
<b>Emitter cut-off current</b>	$I_{EBO}$	$V_{EB} = -3V, I_C=0$		-0.1	$\mu A$
<b>DC current gain</b>	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -50mA$	200	350	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -500mA$	50		
<b>Collector-emitter saturation voltage</b>	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.6	V
<b>Base-emitter saturation voltage</b>	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-1.2	V
<b>Transition frequency</b>	$f_T$	$V_{CE} = -6V, I_C = -20mA$ $f=30MHz$	150		MHz

## Typical Characteristics

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<b>UNIT</b>	A				D	E		A <sub>1</sub>	
<b>mm</b>	1.40 (								